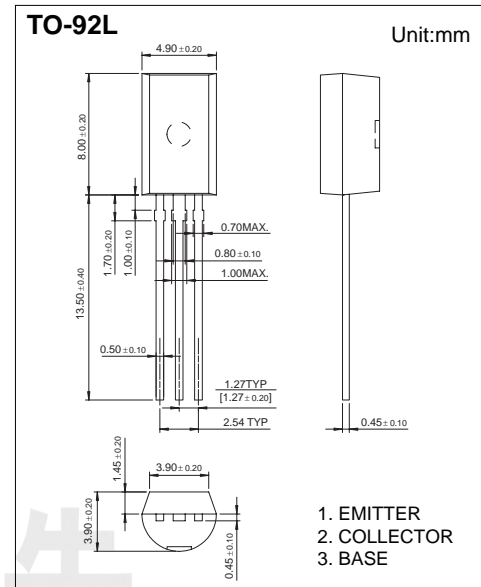


Transistor

NPN Transistors D882

■ Features

- High current output up to 3A
- Low saturation voltage
- Complement to B772



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	40	V
Collector - Emitter Voltage	V_{CE0}	30	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_C	3	A
Collector Current - Pulse	I_{CP}	7	
Base Current	I_B	0.6	
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	

Transistor

NPN Transistors D882

Electrical Characteristics $T_a = 25^\circ\text{C}$

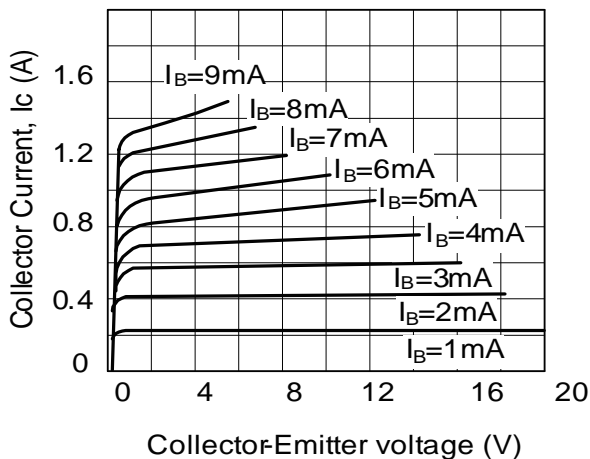
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_C = 100 \mu\text{A}, I_E = 0$	40			V
Collector-emitter breakdown voltage	V_{CE0}	$I_C = 1 \text{ mA}, I_B = 0$	30			
Emitter-base breakdown voltage	V_{EB0}	$I_E = 100 \mu\text{A}, I_C = 0$	5			
Collector cut-off current	I_{CB0}	$V_{CB} = 30 \text{ V}, I_E = 0$			1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = 3 \text{ V}, I_C = 0$			1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2 \text{ A}, I_B = 200 \text{ mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 2 \text{ A}, I_B = 200 \text{ mA}$			2	
DC current gain	$h_{FE(1)}$	$V_{CE} = 2 \text{ V}, I_C = 20 \text{ mA}$	30			
	$h_{FE(2)}$	$V_{CE} = 2 \text{ V}, I_C = 1 \text{ A}$	100		400	
Output capacitance	C_{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		45		pF
Transition frequency	f_T	$V_{CE} = 6 \text{ V}, I_C = 20 \text{ mA}, f = 30 \text{ MHz}$		80		MHz

Classification of $h_{FE(2)}$

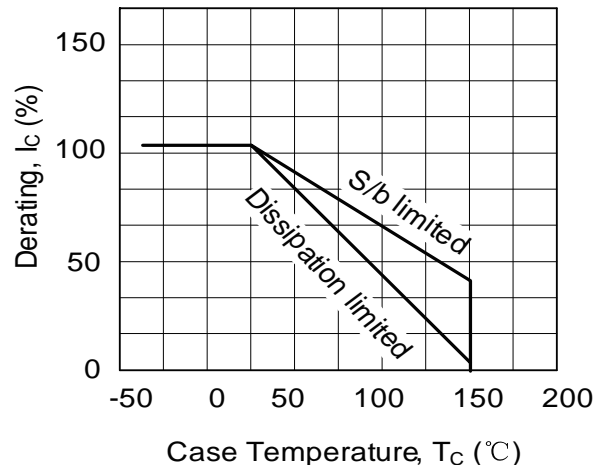
Rank	Q	P	E
Range	100-200	160-320	200-400

Typical Characteristics

Static Characteristics



Derating Curve of Safe Operating Areas



Transistor

NPN Transistors

D882

■ Typical Characteristics

